



ME 553 Final Project

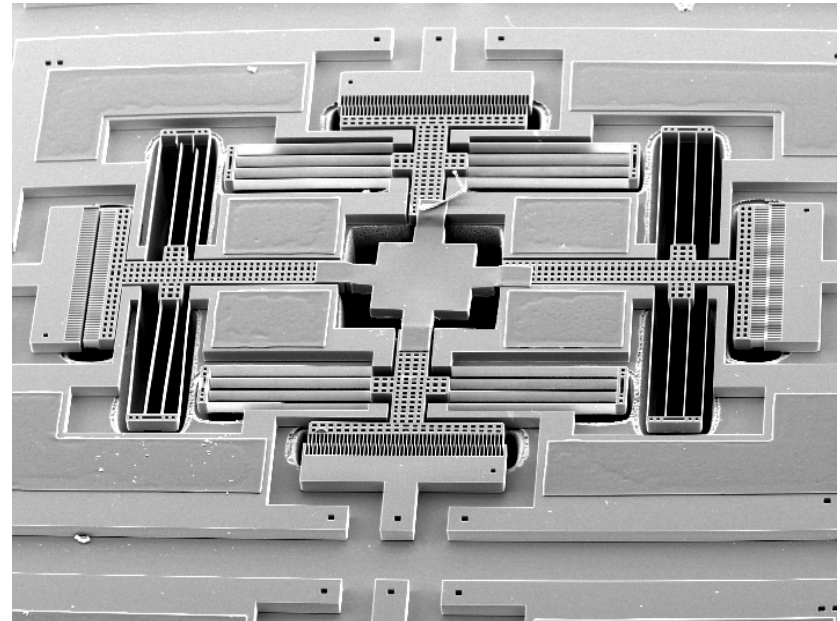
University of Michigan College of Engineering

Piezoresistive Sensor Design for Single Layer PDMS on Silicon Hybrid Micro Actuator with Multi Axis Out of Plane Motion Capabilities

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Motivation

- ❑ Use of PDMS in Mems.
- ❑ Out of plane actuation.
- ❑ Useful applications.
- ❑ High Bandwidth.



Project Goal

Precise control of hybrid Actuator.

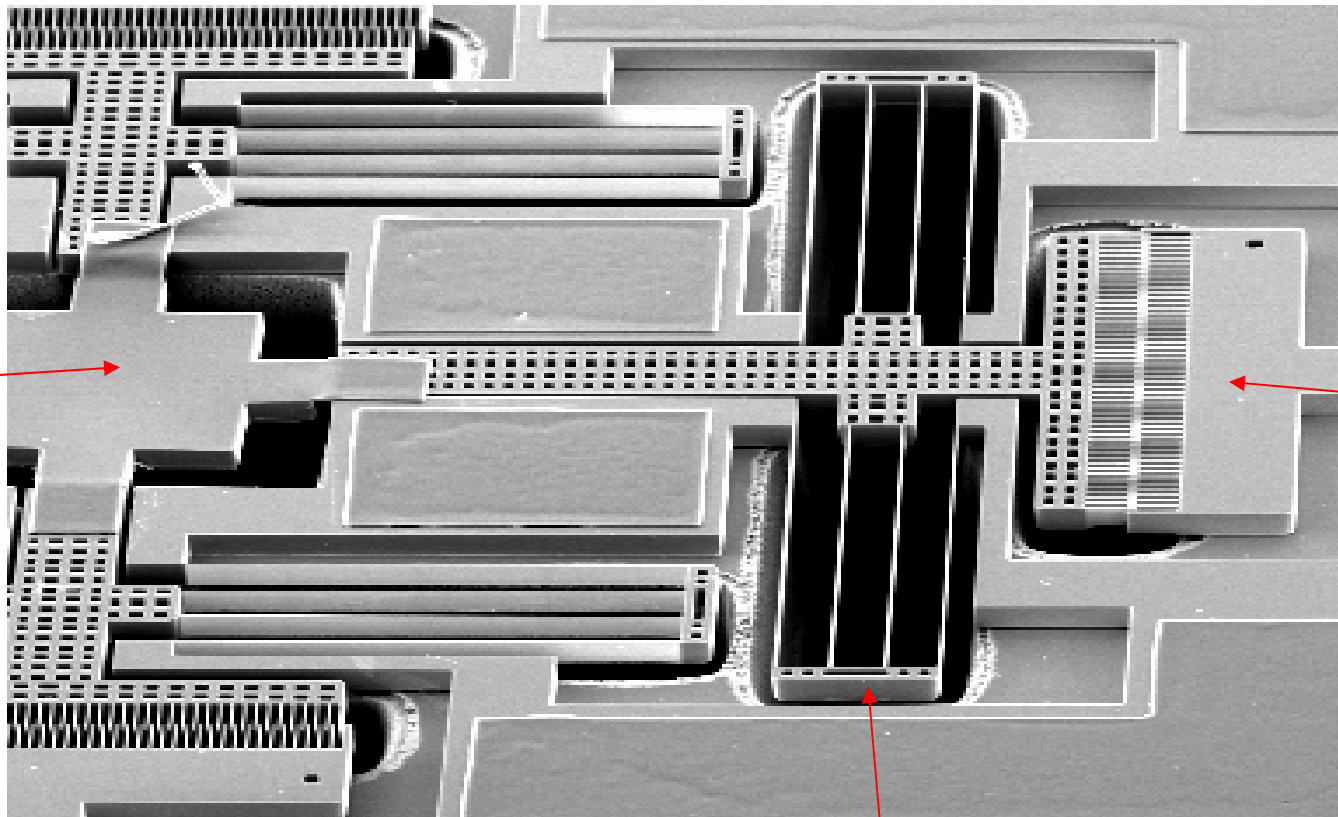
Objectives:

- Design a sensor using the existing structure.
- Propose fabrication strategy.
- Parametric study of sensor.
- Design optimization.

Problem Setup

- ❑ Manufacturability.
- ❑ Structural compatibility of sensor to the platform.
- ❑ Capacitive / Resistive Sensor. Pros & Cons.
- ❑ Analysis of the sensor characteristics e.g. sensitivity, Bandwidth

Proposed Solution



Platform

Comb
Drive
Actuator

Folded Flexure Beam

Cantilever Fabrication



Silicon Cantilever
beam ready to be
fabricated into
Piezoresistive
sensor.

KEY:



Processing: Piezoresistor B+

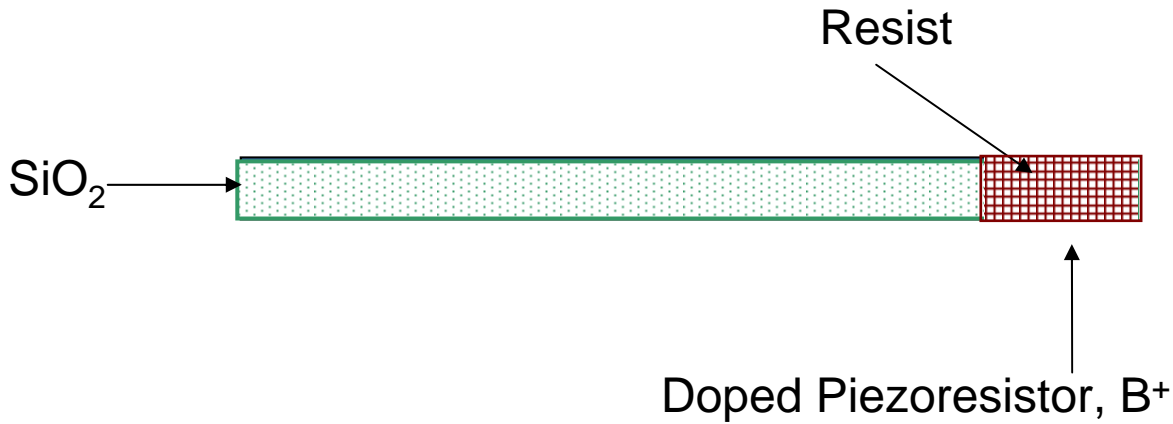


Cantilever beam is lightly doped by Piezoresistor, B+ Using oblique ion doping.

KEY:

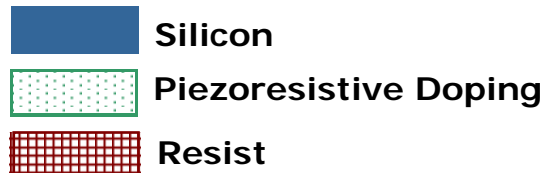


Processing: Resist

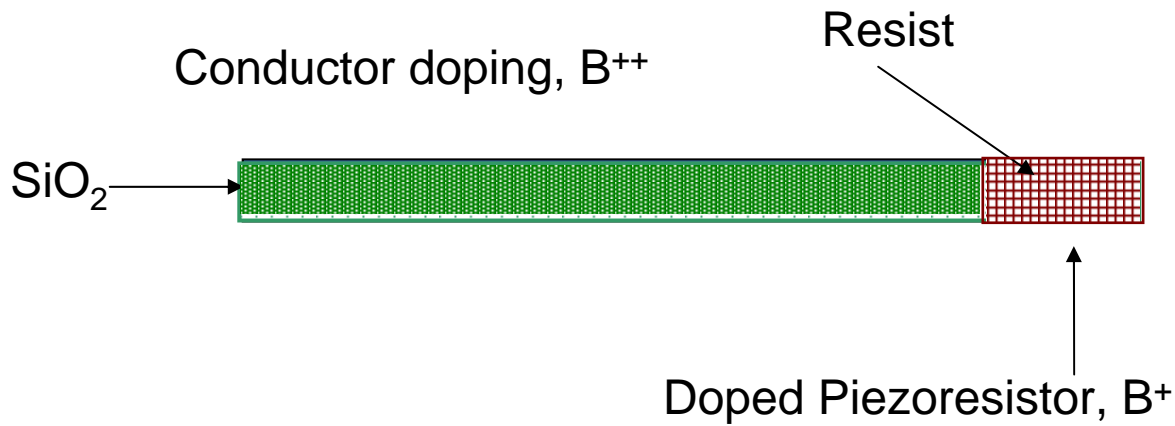


Resist is applied to heavily dope the beam.

KEY:







Processing: Conductor B++

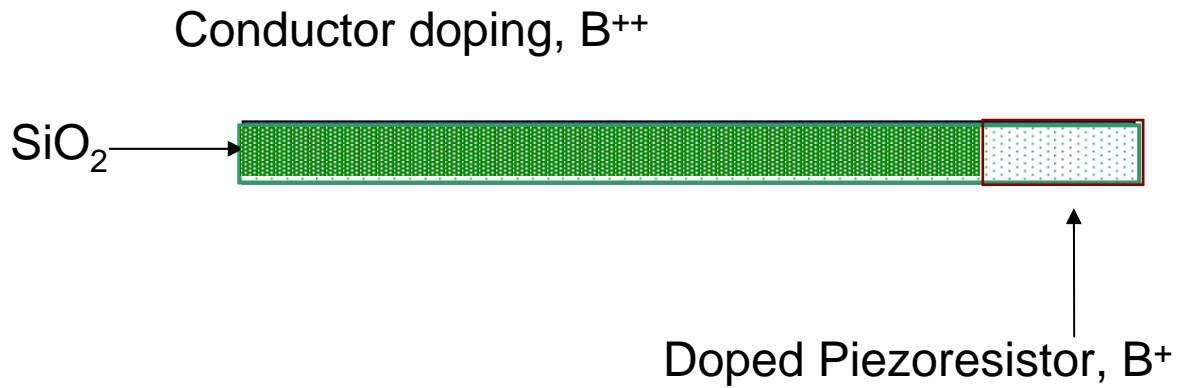


Oblique ion doping is applied again to heavily dope the desired portion.

KEY:

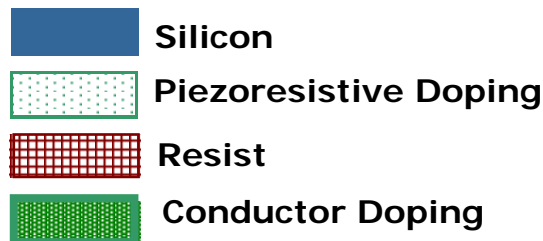
-  Silicon
-  Piezoresistive Doping
-  Resist
-  Conductor Doping

Cantilever Fabrication



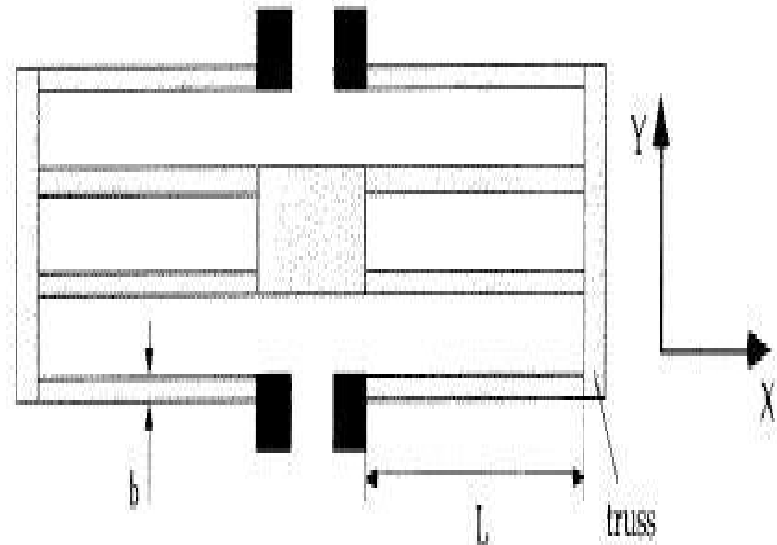
Final structure with Piezoresistor B⁺ and conductive B⁺⁺.

KEY:



Sensor Design

- ❑ Folded Flexural Beams Modeling.
- ❑ Piezoresistive Expression.
- ❑ Wheatstone bridge Analysis.



Flexure Beam Modeling

- Actuating force

$$F_e = \frac{2 \epsilon^2 V^2}{g}$$

- Deflection

$$u(x) = \frac{F_e}{8EI} \left(\frac{L}{2} x^2 - \frac{1}{3} x^3 \right)$$

- Stress

$$\sigma(x) = \frac{10^8}{3.6} \left(\frac{L}{2} - x \right) V^2$$

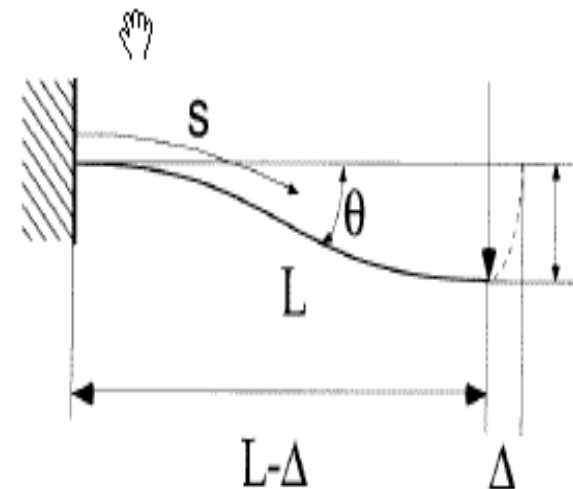
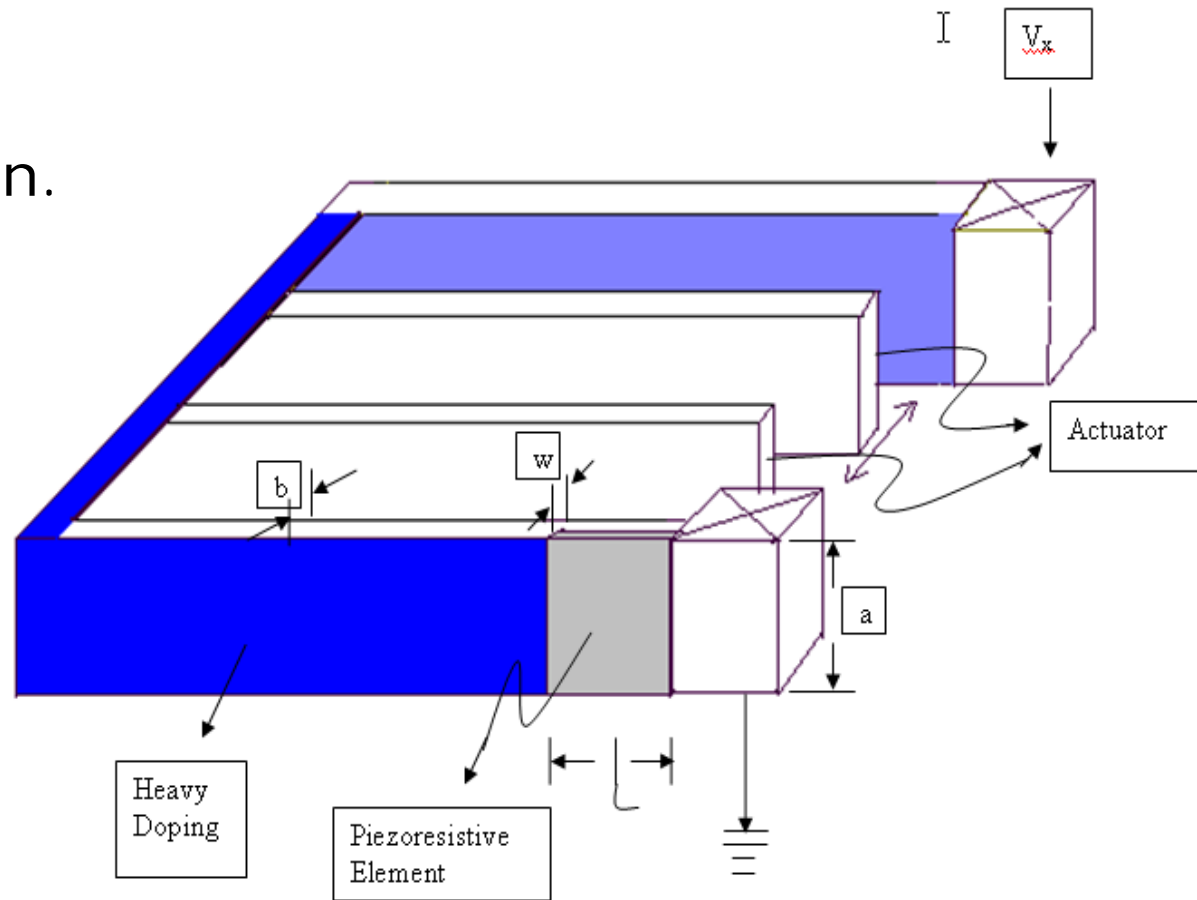


Figure A1. Sketch of clamped-guided beam including parameters.

Piezoresistive Expression

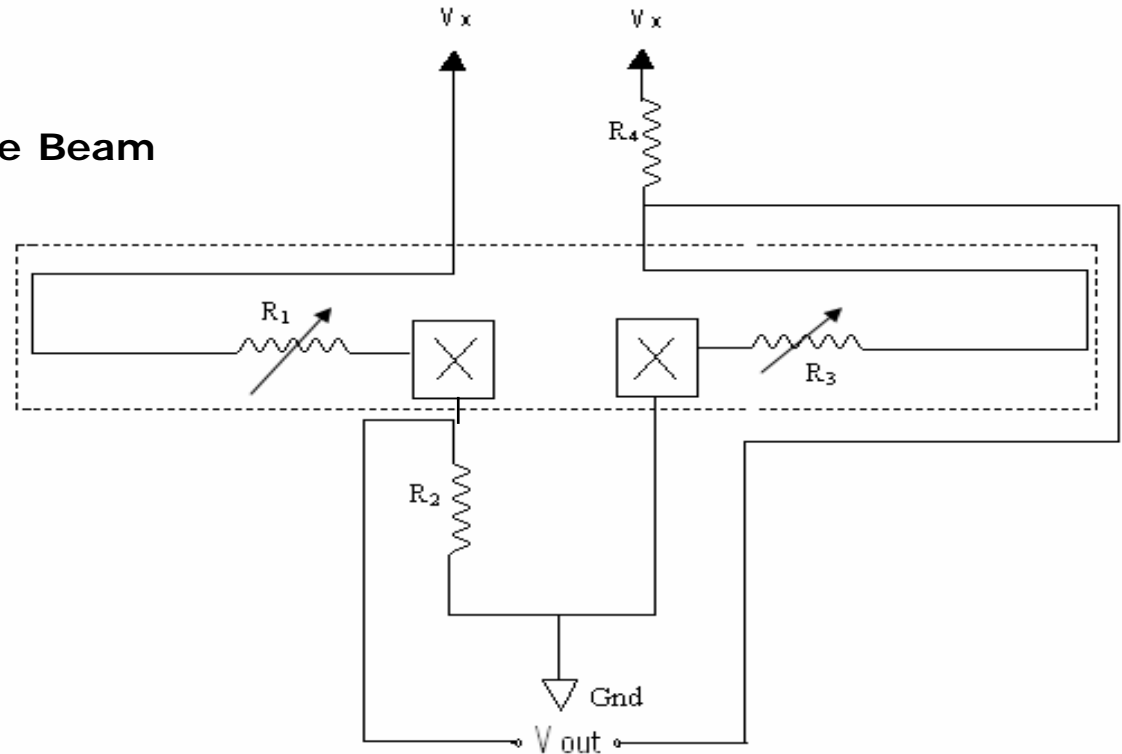
- Assuming:
 - [110] direction.

$$\frac{d\Delta R(V, x)}{dRo} = \frac{\pi_{110} \pi_{100}^2}{3.6} \left(\frac{L}{2} - x \right)$$



Electrical Circuit Analysis

Circuit Embedded on the Beam



$$V_{out} = \frac{1}{2} \left(\frac{\Delta R}{R_0} \right) V_x$$

$$V_{out}(u) = \frac{1.258 \times \pi \times 10^{-6} E}{\omega} (5 \times 10^{-4} l - l^2) u$$

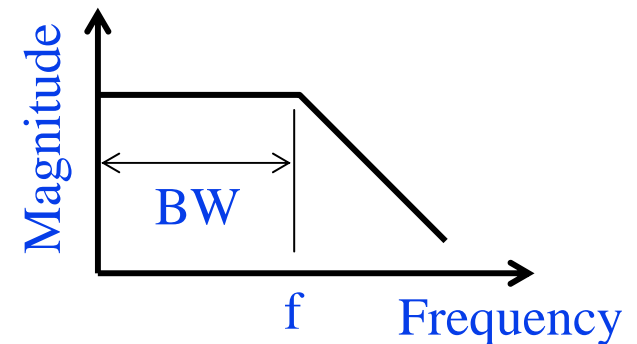
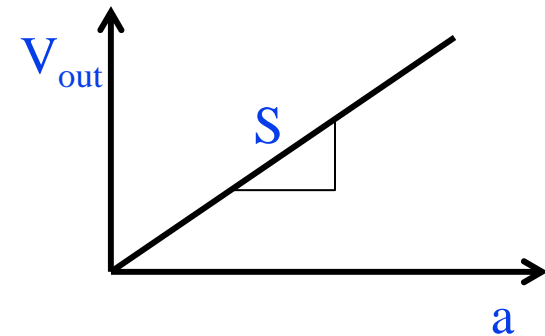
Optimization

- ❑ Sensitivity Analysis
 - Actuator voltage
 - Displacement

- ❑ SCR optimization
 - Piezoresistors geometry

- ❑ Bandwidth Sensitivity Tradeoff
 - First natural frequency
 - Overall system bandwidth

- ❑ Effect of Noise and MDD
 - Johnson's noise



Results

- ❑ Tradeoff between Bandwidth and Sensitivity
 - We require sensitivity optimization
 - Inherent need due to high bandwidth actuation.

- ❑ Different Design Parameters effect Different Sensor Characteristics:
 - Cross-sectional Parameter (a,w): affects Sensitivity
 - Longitudinal Length Ratio (L): affects Bandwidth
 - SCR affects sensitivity

Future Work

- ❑ Transfer Function or State space Relationships for the System.
- ❑ Control Algorithm for Nano-positioning of the platform.
- ❑ Use of the platform in exciting Applications like the scanning probe microscope.

Questions?

